L	Hits	Search Text	DB	Time stamp
Number				
1	323	semiconductor and (complementary adj	USPAT;	2004/02/25
		bipolar adj transistor)	US-PGPUB;	14:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	143	(semiconductor and (complementary adj	USPAT;	2004/02/25
-		bipolar adj transistor)) and electrode	US-PGPUB;	14:25
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	131		USPAT;	2004/02/25
	Ì	bipolar adj transistor)) and electrode)	US-PGPUB;	14:25
		and emitter and base and collector	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	83	(((semiconductor and (complementary adj	USPAT;	2004/02/25
	1	bipolar adj transistor)) and electrode)	US-PGPUB;	14:26
		and emitter and base and collector) and	EPO; JPO;	
	1	((polycrystal\$4 adj (silicon or si)) or	DERWENT;	
		polysilicon)	IBM TDB	

L	Hits	Search Text	DB	Time stamp
Number				<u> </u>
1	35603	_semiconductor and-(bipolar adj	USPAT;	2004/02/25
]		transistor)	US-PGPUB;	14:49
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
2	9672	(semiconductor and (bipolar adj	USPAT;	2004/02/25
-		transistor)) and ((polycrystal\$4 adj	US-PGPUB;	14:50
		(silicon or si)) or polysilicon)	EPO; JPO;	
			DERWENT;	
	,		IBM TDB	
3	534	((semiconductor and (bipolar adj	USPAT;	2004/02/25
		transistor)) and ((polycrystal\$4 adj	US-PGPUB;	14:51
		(silicon or si)) or polysilicon)) and	EPO; JPO;	1
		(rapid adj thermal adj anneal\$3)	DERWENT;	
		_w	IBM TDB	
14	6	(((semiconductor and (bipolar adj	USPAT;	2004/02/25
1 '		transistor)) and ((polycrystal\$4 adj	US-PGPUB;	14:51
		(silicon or si)) or polysilicon)) and	EPO; JPO;	
		(rapid adj thermal adj anneal\$3)) and	DERWENT;	
		(residual adj oxide)	IBM TDB	